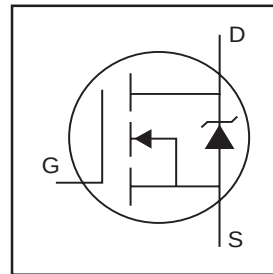


IRLR2705PbF IRLU2705PbF

HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Ultra Low On-Resistance
- Surface Mount (IRLR2705)
- Straight Lead (IRLU2705)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



$$V_{DS} = 55V$$

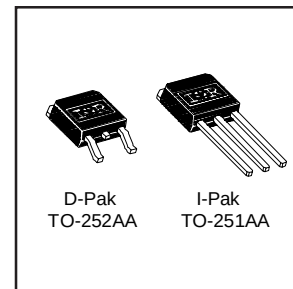
$$R_{DS(on)} = 0.040\Omega$$

$$I_D = 28A^{\textcircled{5}}$$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	28	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	20	
I_{DM}	Pulsed Drain Current $\textcircled{1}$	110	
$P_D @ T_C = 25^\circ C$	Power Dissipation	68	W
	Linear Derating Factor	0.45	W/ $^\circ C$
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy $\textcircled{2}$	110	mJ
I_{AR}	Avalanche Current $\textcircled{3}$	16	A
E_{AR}	Repetitive Avalanche Energy $\textcircled{3}$	6.8	mJ
dv/dt	Peak Diode Recovery dv/dt $\textcircled{3}$	5.0	V/ns
T_J	Operating Junction and	-55 to +175	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

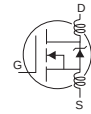
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.2	$^\circ C/W$
$R_{\theta JA}$	Case-to-Ambient (PCB mount)**	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

** When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.065	—	V/°C	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.040	W	$V_{GS} = 10V, I_D = 17A$ ④
		—	—	0.051		$V_{GS} = 5.0V, I_D = 17A$ ④
		—	—	0.065		$V_{GS} = 4.0V, I_D = 14A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	11	—	—	S	$V_{DS} = 25V, I_D = 16A$ ⑦
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	25	nC	$I_D = 16A$
Q_{gs}	Gate-to-Source Charge	—	—	5.2		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	14		$V_{GS} = 5.0V$, See Fig. 6 and 13 ④ ⑦
$t_{d(on)}$	Turn-On Delay Time	—	8.9	—	ns	$V_{DD} = 28V$
t_r	Rise Time	—	100	—		$I_D = 16A$
$t_{d(off)}$	Turn-Off Delay Time	—	21	—		$R_G = 6.5\Omega, V_{GS} = 5.0V$
t_f	Fall Time	—	29	—		$R_D = 1.8\Omega$, See Fig. 10 ④ ⑦
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑥
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	880	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	220	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	94	—		$f = 1.0MHz$, See Fig. 5 ⑦



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	28	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	110		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 17A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	76	110	ns	$T_J = 25^\circ\text{C}, I_F = 16A$
Q_{rr}	Reverse Recovery Charge	—	190	290	nC	$di/dt = 100A/\mu s$ ④ ⑦
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 610\mu H$
 $R_G = 25\Omega, I_{AS} = 16A$. (See Figure 12)
- ③ $I_{SD} \leq 16A$, $di/dt \leq 270A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

- ⑤ Calculated continuous current based on maximum allowable junction temperature; Package limitation current = 20A.
- ⑥ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact.
- ⑦ Uses IRLZ34N data and test conditions.

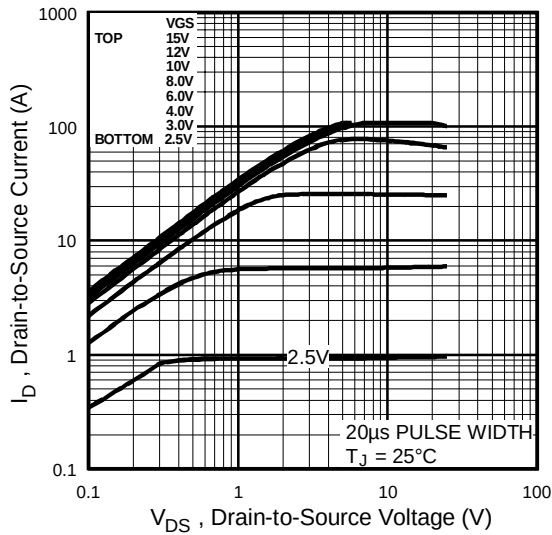


Fig 1. Typical Output Characteristics

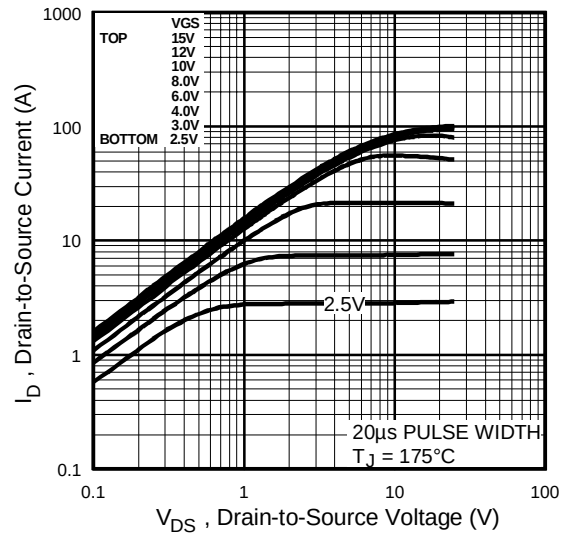


Fig 2. Typical Output Characteristics

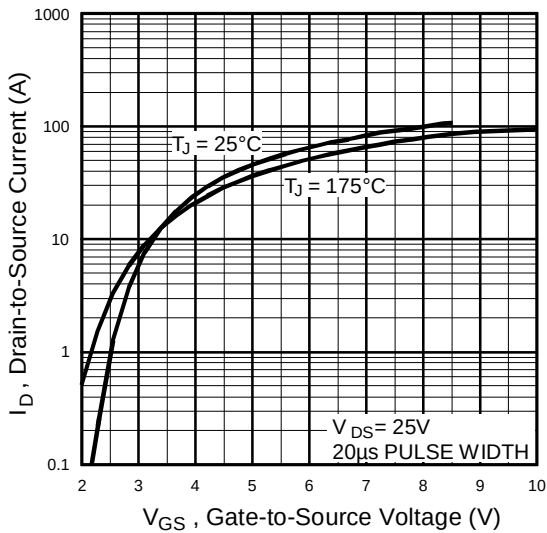


Fig 3. Typical Transfer Characteristics

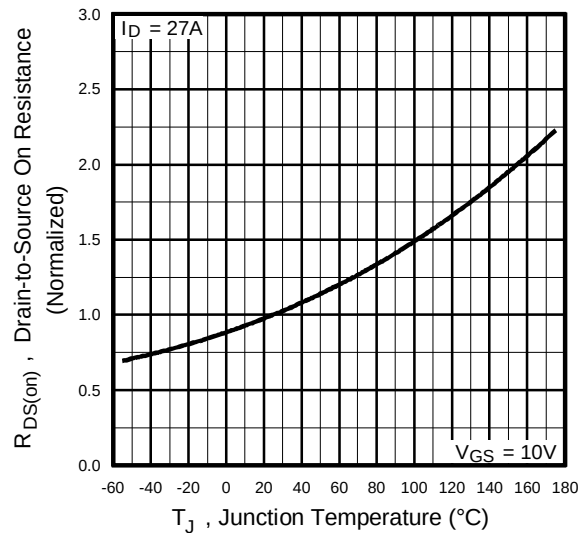


Fig 4. Normalized On-Resistance Vs. Temperature

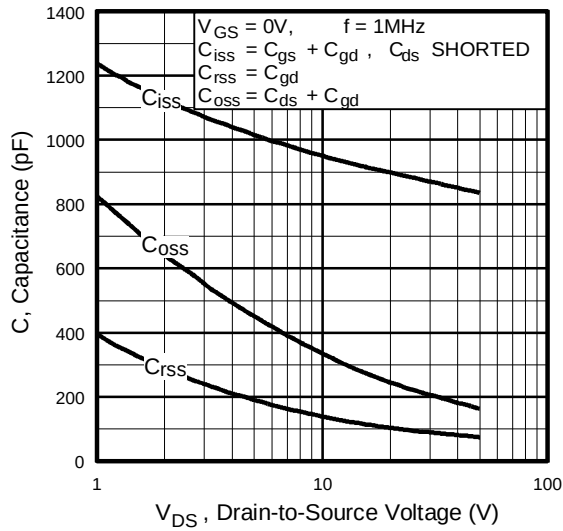


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

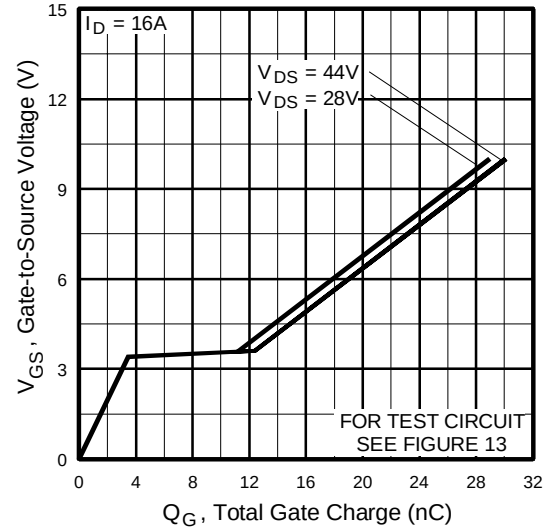


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

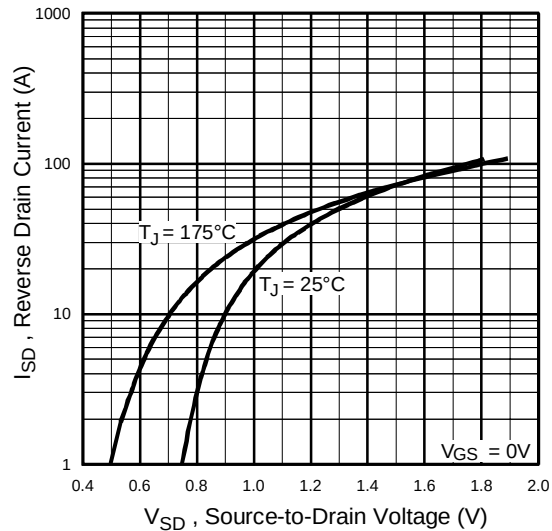


Fig 7. Typical Source-Drain Diode Forward Voltage

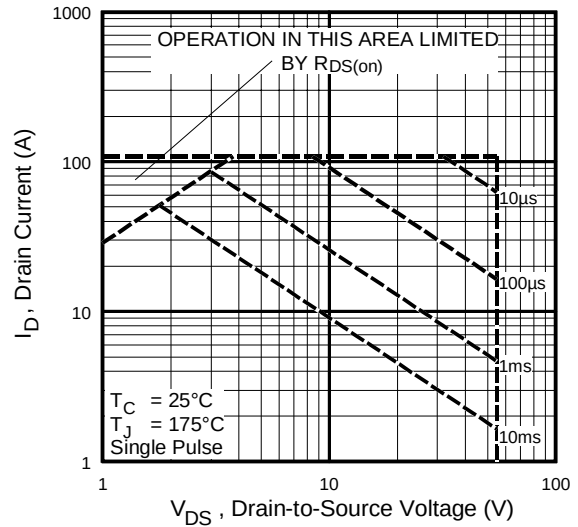


Fig 8. Maximum Safe Operating Area

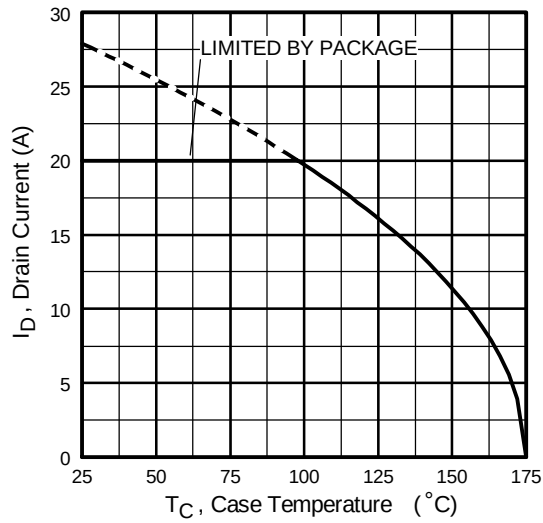


Fig 9. Maximum Drain Current Vs. Case Temperature

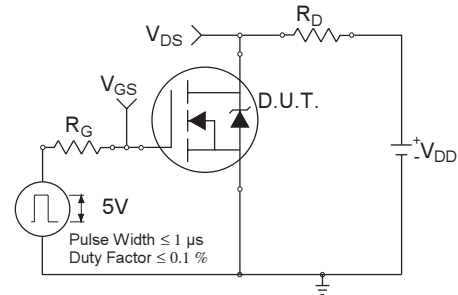


Fig 10a. Switching Time Test Circuit

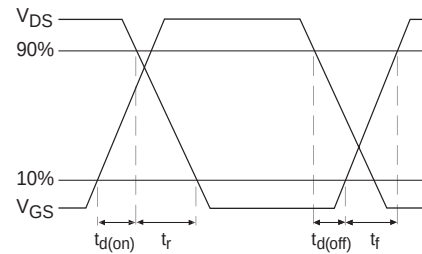


Fig 10b. Switching Time Waveforms

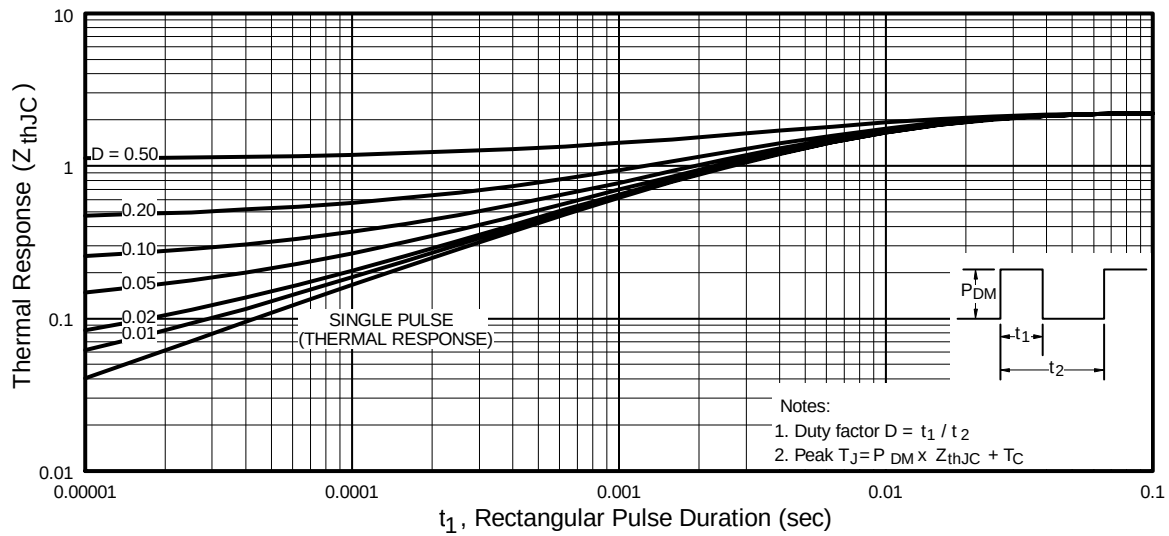


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

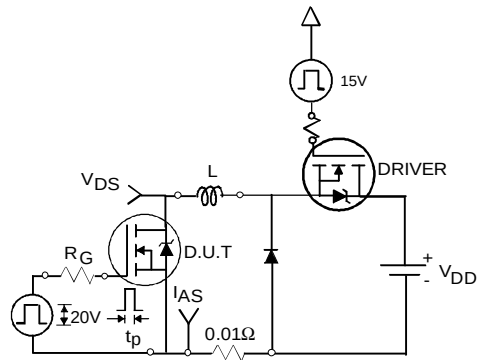


Fig 12a. Unclamped Inductive Test Circuit

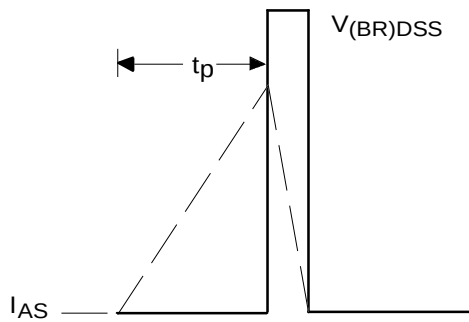


Fig 12b. Unclamped Inductive Waveforms

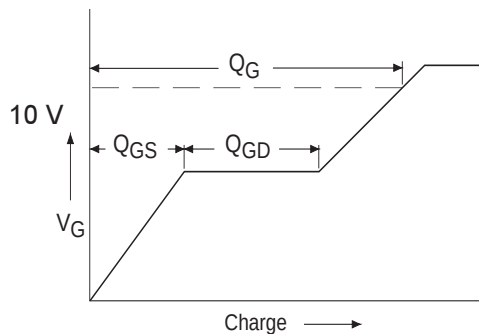


Fig 13a. Basic Gate Charge Waveform

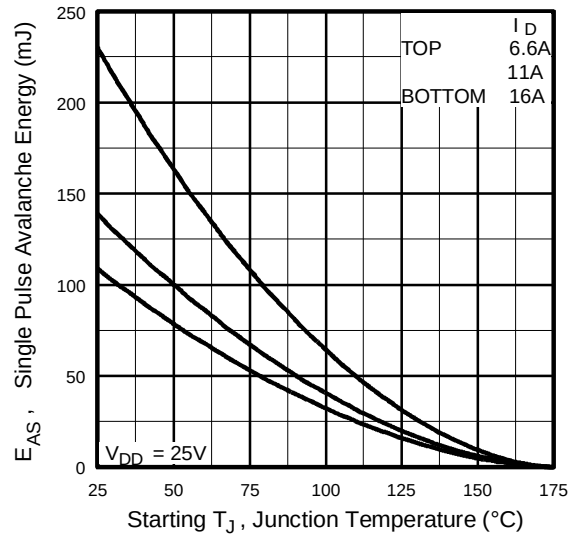


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

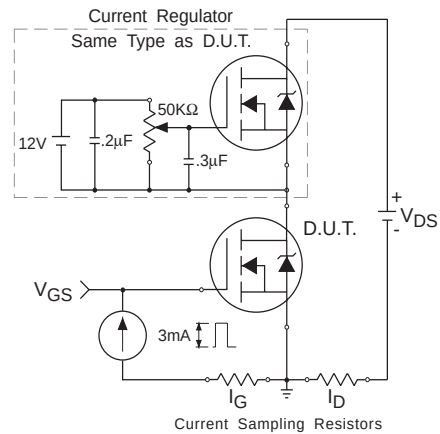
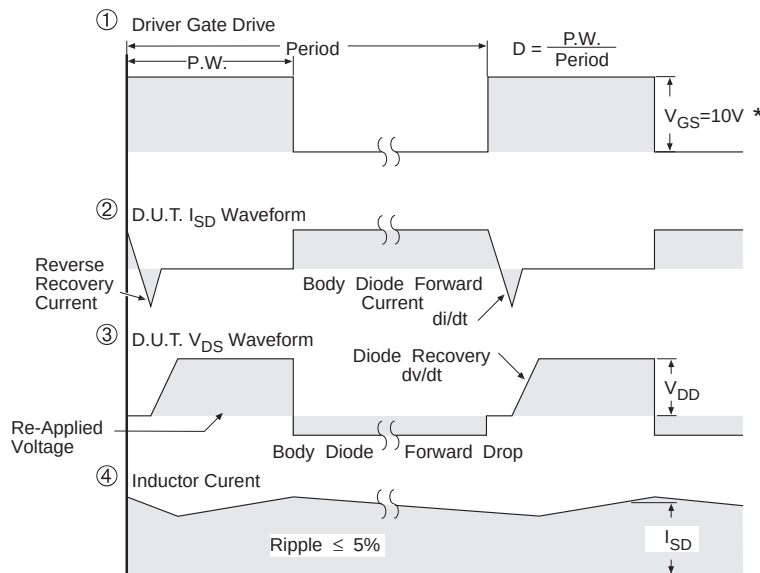
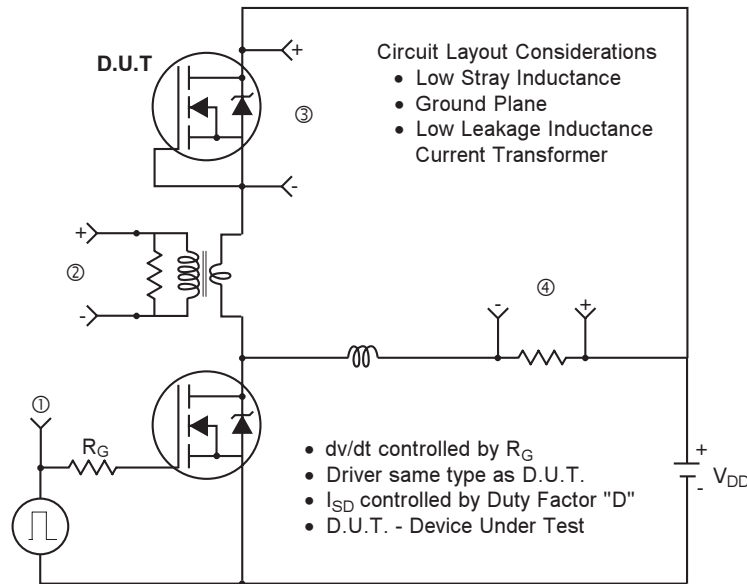


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

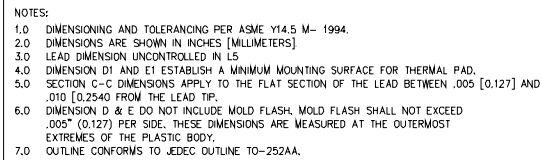


* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

International
IOR Rectifier

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.15			
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	1.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
C1	0.41	0.58	.016	.022	5
c2	.040	0.08	.018	0.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	—	.205	—	4
E	6.35	6.73	.250	.265	6
e	4.32	—	.170	—	4
E1	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 REF.		.108 REF.		
L2	.051 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	

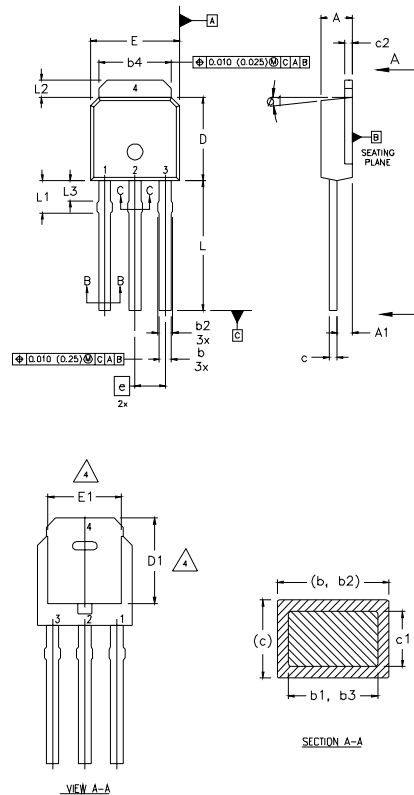
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

Diagram illustrating the markings on the IRFU120 package:

- INTERNATIONAL RECTIFIER LOGO**: Points to the IR logo on the package.
- PART NUMBER**: Points to the text **IRFU120** on the package.
- DATE CODE**: Points to the text **P916A** on the package.
- P = DESIGNATES LEAD-FREE PRODUCT (OPTIONAL)**: Points to the letter **P** in the date code.
- YEAR 9 = 1999**: Points to the digit **9** in the date code.
- WEEK 16**: Points to the number **16** in the date code.
- A = ASSEMBLY SITE CODE**: Points to the letter **A** in the date code.
- ASSEMBLY LOT CODE**: Points to the number **12** and **34** on the package.

I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
5. LEAD DIMENSION UNCONTROLLED IN L3.
6. DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
7. OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
8. CONTROLLING DIMENSION : INCHES.

LEAD ASSIGNMENTS

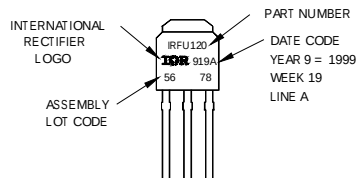
HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

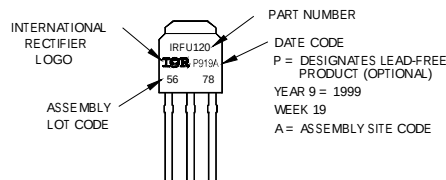
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	Ø	15°	Ø	15°	

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 1999
IN THE ASSEMBLY LINE "A"
Note: "P" in assembly line
position indicates "Lead-Free"



OR

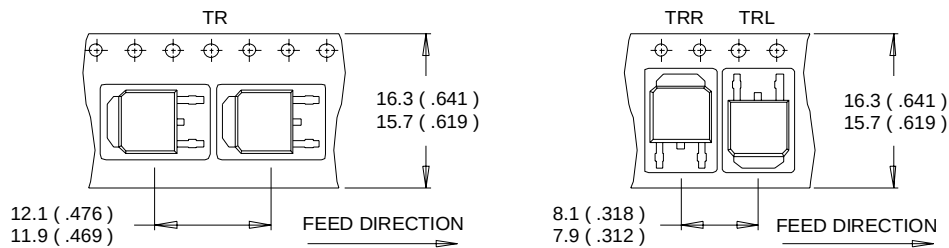


IRLR/U2705PbF

International
IR Rectifier

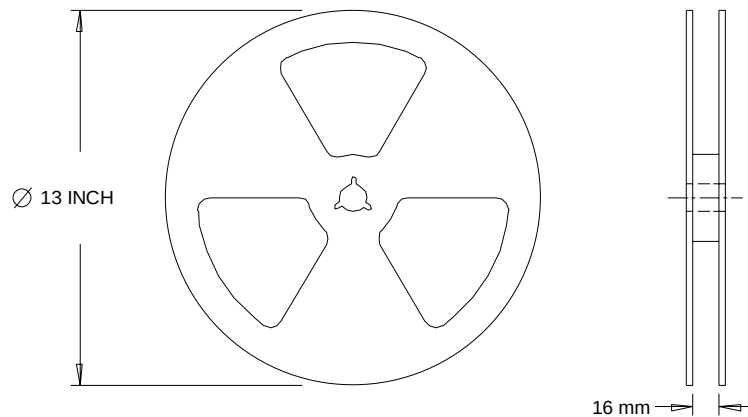
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.01/05

www.irf.com

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>